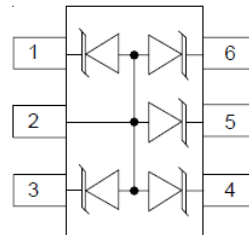


Low Capacitance TVS Diode Array

SOT-666



MARKING: J



Features

- ◇ 100W (8/20 μ s) Peak Pulse Power
- ◇ ESD and Latch-Up Protection
- ◇ SOT-563 Package
- ◇ RoHS Compliant
- ◇ Matte Tin Lead finish (Pb-Free)
- ◇ Protect Five I/O Lines
- ◇ Meet IEC61000-4-2 Level 4:
 - Contact Discharge > 25kV Air
 - Discharge > 25kV

Applications

- ◇ Peripherals
- ◇ Audio Players
- ◇ Digital Cameras
- ◇ Cordless Phones
- ◇ Portable Instrumentation
- ◇ Notebooks and Handhelds
- ◇ Personal Digital Assistants (PDA's)
- ◇ Cellular Handsets and Accessories

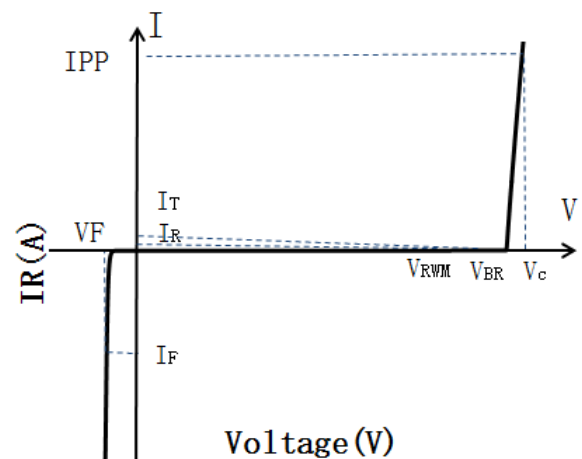
Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
PPK	Peak Pulse Power	100	W
IPP	Peak Pulse Current	6	A
VESD (Contact)	Contact ESD Voltage per IEC61000-4-2	25	kV
VESD (Air)	Air ESD Voltage per IEC61000-4-2	25	kV
TJ	Junction Temperature	-55 to +125	°C
TSTG	Storage Temperature	-55 to +150	°C

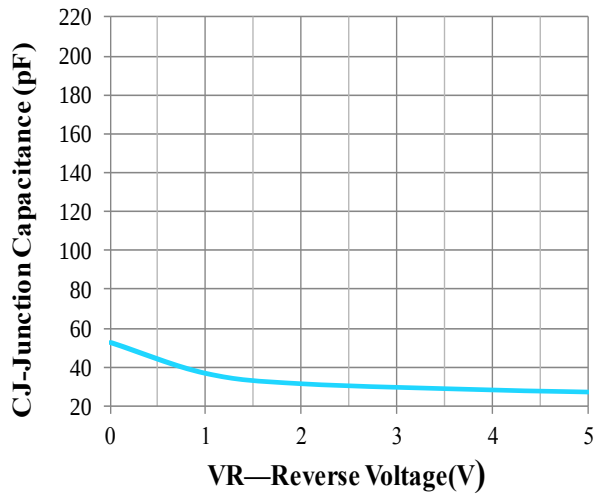
Electrical Characteristics (TA=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRWM	Reverse Working Peak Voltage				5	V
VBR	Reverse Breakdown Voltage	IT = 1mA	6		8	V
IR	Reverse Leakage Current	VRWM = 5V			1	μA
VC	Clamping Voltage	IPP = 1A (8/20μs)			10	V
VC	Clamping Voltage	IPP = 6A (8/20μs)			18	V
CJ	Capacitance	VR = 0V, f = 1MHz		50		pF

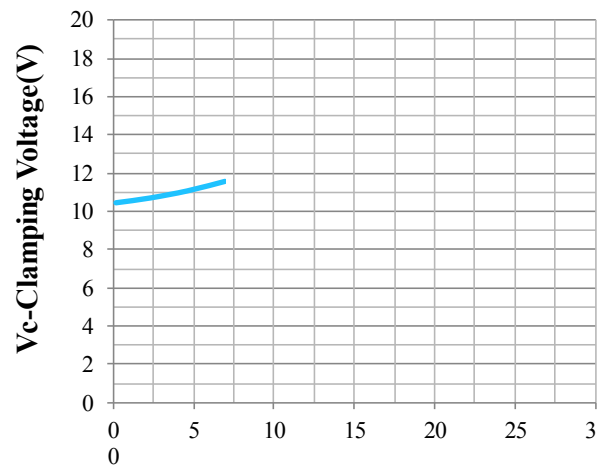
Symbol	Parameter
IT	Test Current
IPP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ic



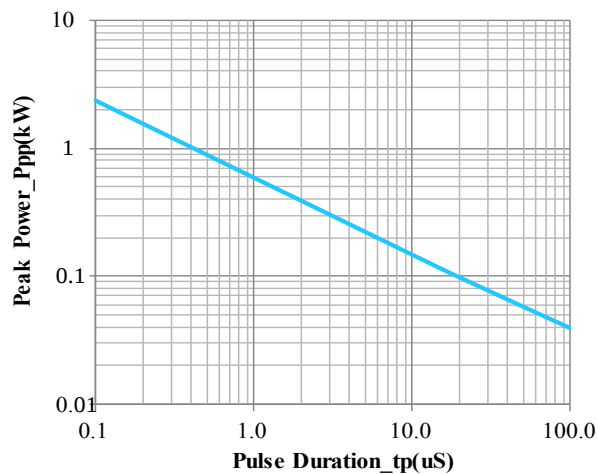
Typical Characteristics



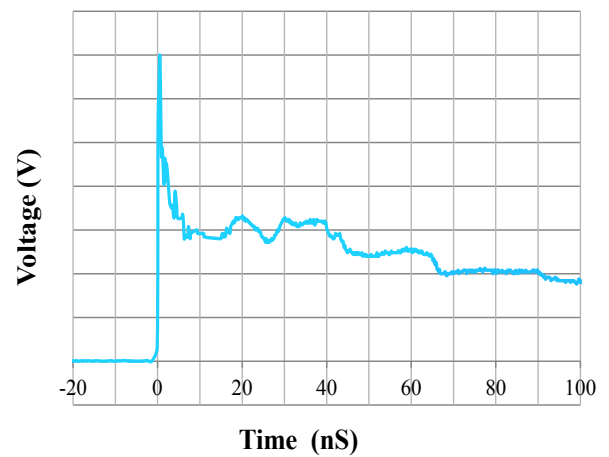
Junction Capacitance vs. Reverse Voltage



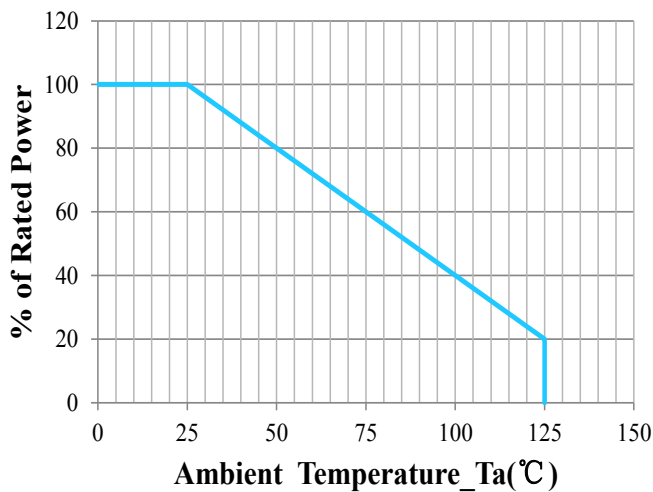
Clamping Voltage vs. Peak Pulse Current



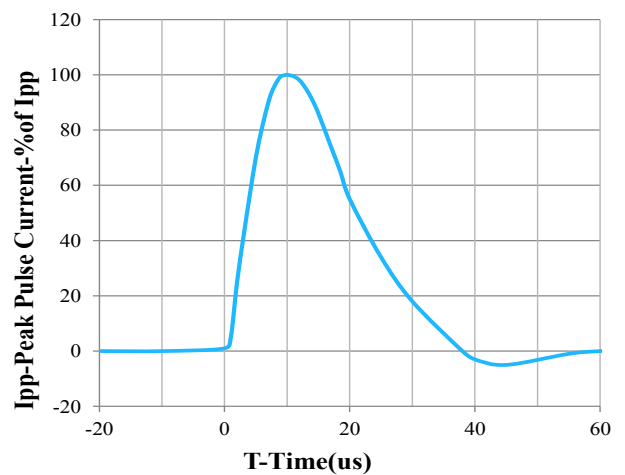
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform



Power Derating Curve



8 X 20us Pulse Waveform

SOT-666 PACKAGE OUTLINE DIMENSIONS

